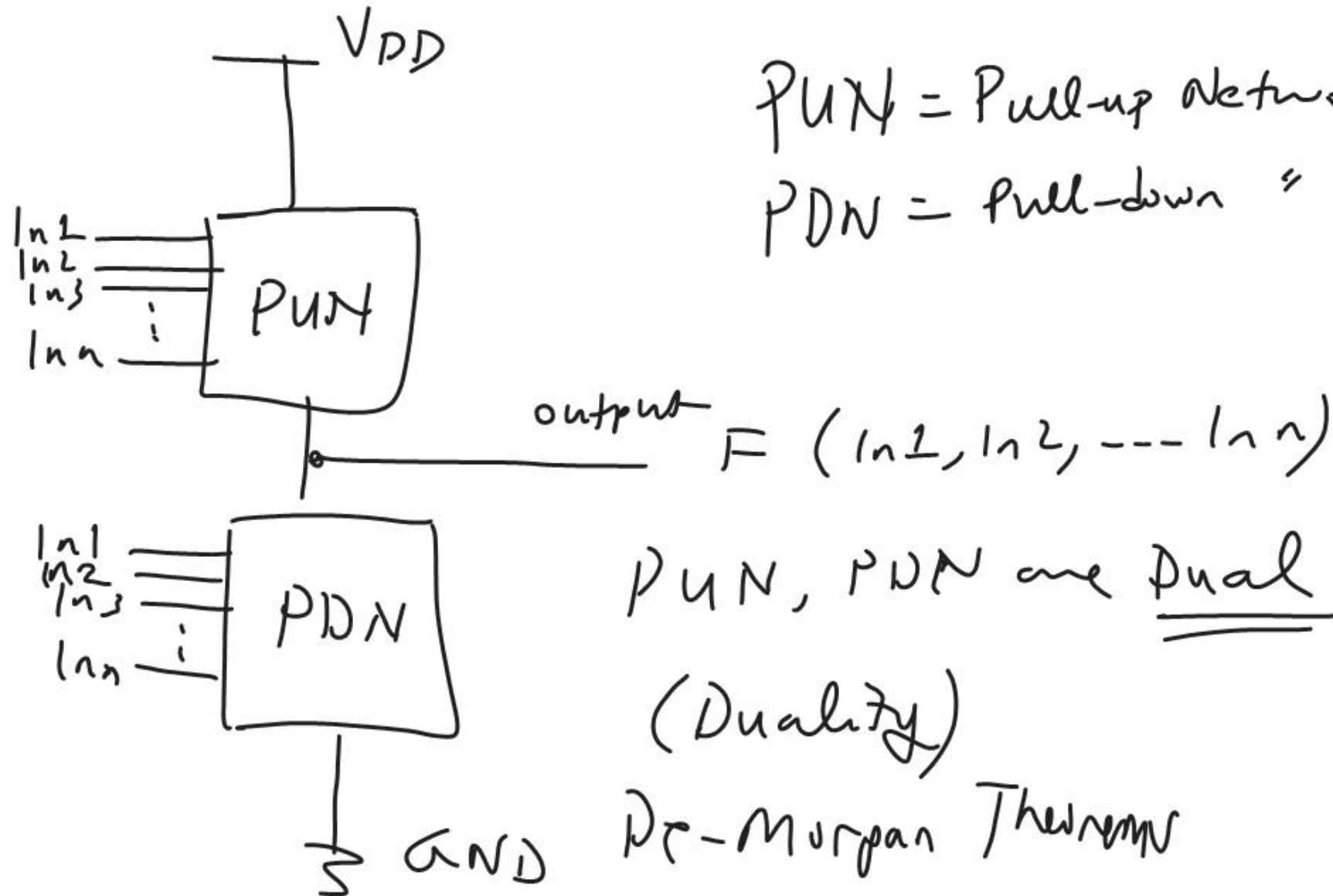


CMOS COMBINATIONAL NETWORKS

03.12.2010
©



Boolean Algebra

$$\overline{\overline{X}} = X$$

$$1 + X = 1 \quad , \quad 1 \cdot X = X \quad , \quad X + X = X$$

$$0 \cdot X = 0 \quad \quad 0 + X = X \quad \quad X \cdot X = X$$

$$\left. \begin{array}{l} \overline{X+Y} = \overline{X} \cdot \overline{Y} \\ \overline{X \cdot Y} = \overline{X} + \overline{Y} \end{array} \right\} \text{De-Morgan's Theorem}$$

If the DUAL of the statement is TRUE then it is TRUE

$$\left. \begin{array}{l} X + (Y \cdot Z) = (X + Y) \cdot (X + Z) \\ X \cdot (Y + Z) = X \cdot Y + X \cdot Z \end{array} \right\} \text{Distributive Property}$$

$$X + (Y + Z) = (X + Y) + Z \quad \text{associative property}$$

$$X + Y = Y + X \quad \text{commutative } 4$$

Precedence $\Rightarrow$ NOT, AND, OR

$$x + xy = x$$

$$x \cdot (x+y) = x^2$$

$$x + xy = x \cdot \underbrace{(1+y)}_1 = x$$

$$x \cdot (x+y) = \underbrace{x \cdot x}_x + x \cdot y = x + xy = x \cdot \underbrace{(1+y)}_2 = x^2$$

LOGIC DESIGN

a	b	c	f
---	---	---	---

0 0 0

0

0 0 1

1

→ minterm 1 ⇒ m₁

0 1 0

0

0 1 1

1

⇒ m₂

1 0 0

0

1 0 1

0

1 1 0

1

⇒ m₃

1 1 1

0

bc 00 01 11 10

a

0	0	1	1	0
1	0	0	0	1

Karnaugh map

$$f = \bar{a}c + ab\bar{c}$$

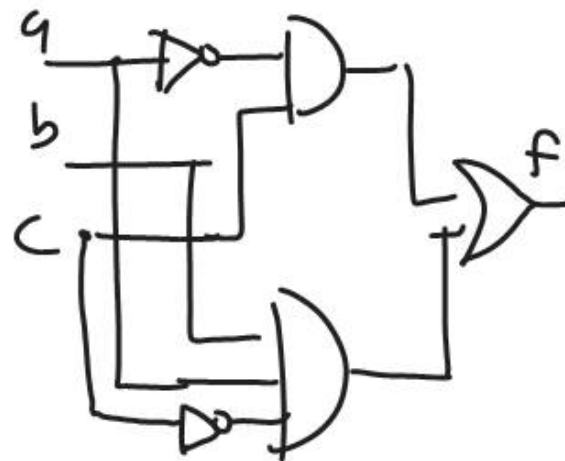
Sum of Products form (SOP)

$$f(a, b, c) = \sum_{i=1}^n m_i$$

$$m_1 = \bar{a}\bar{b}c$$

$$m_2 = \bar{a}bc$$

$$m_3 = ab\bar{c}$$

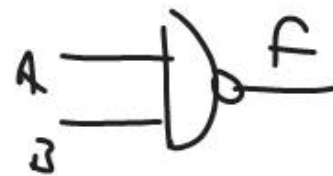
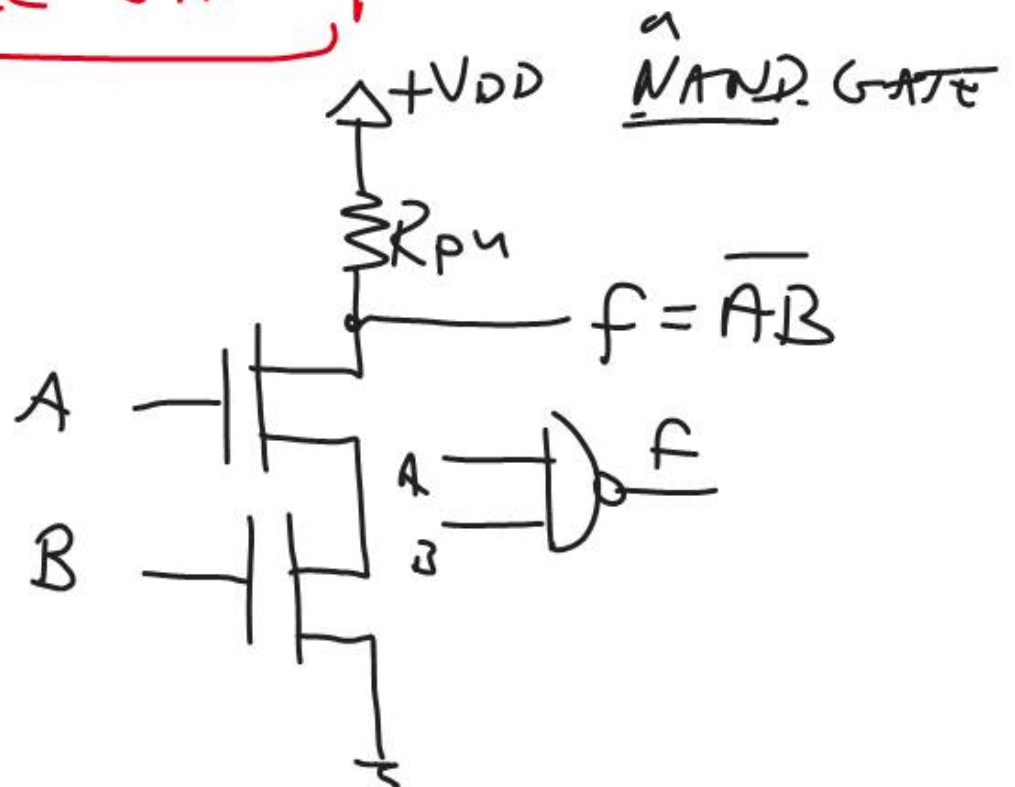
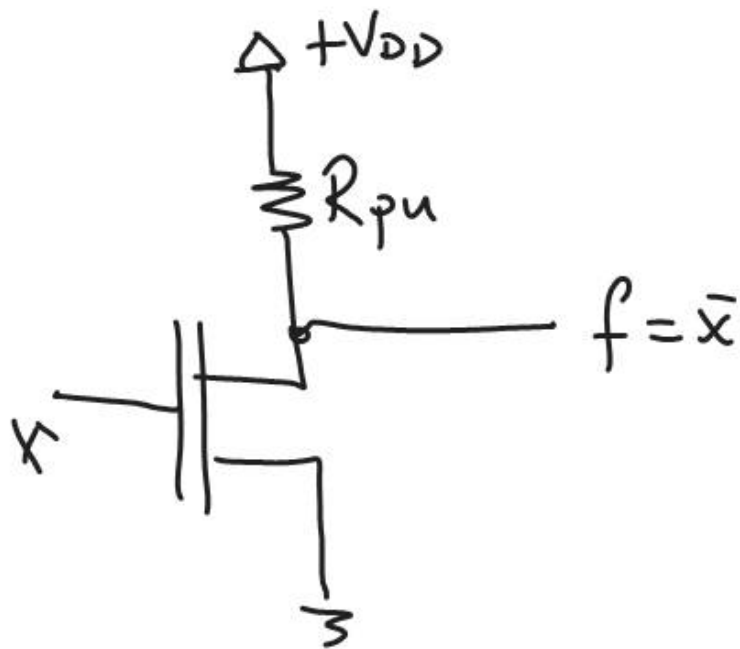


Or, using maxterms

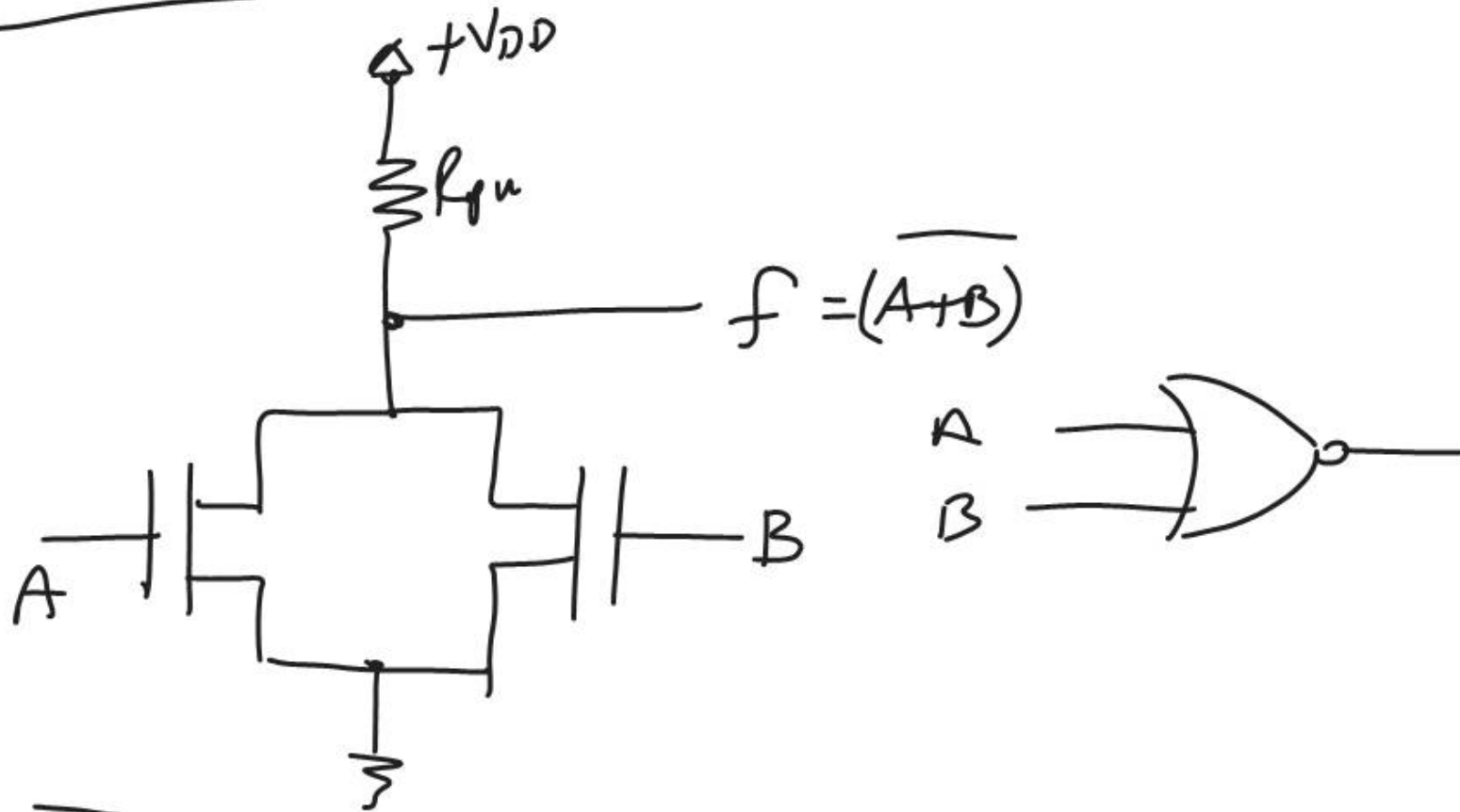
$$f = \prod_{i=1}^n M_i$$

Product of Sums Form
(POS)

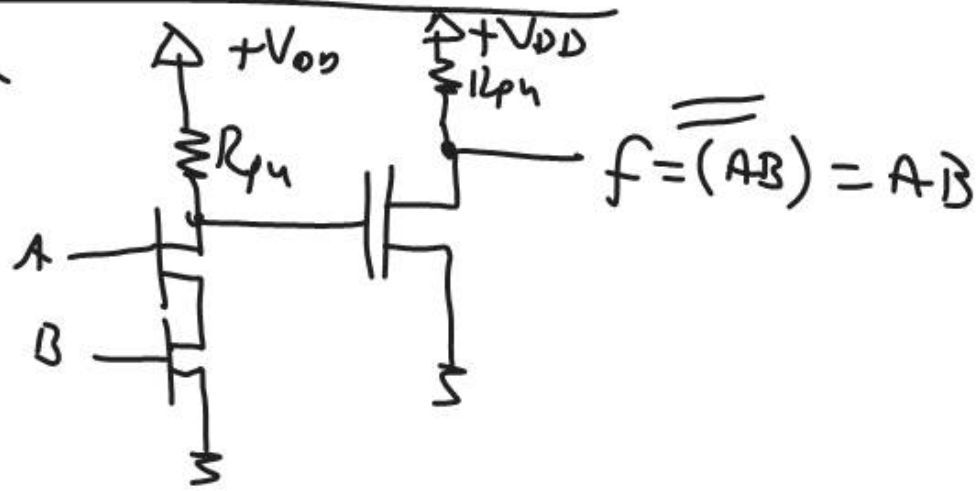
NMOS LOGIC GATES

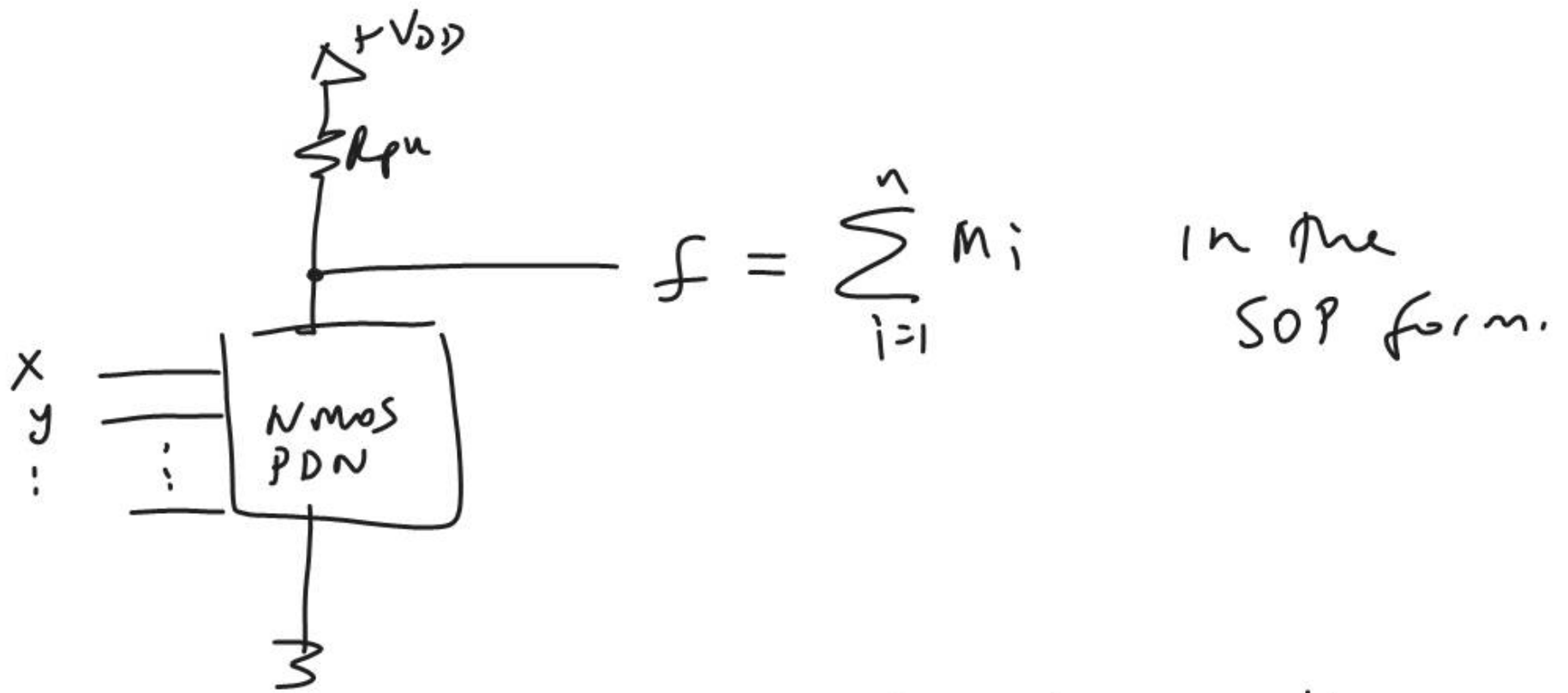


a NOR gate:



an AND Gate

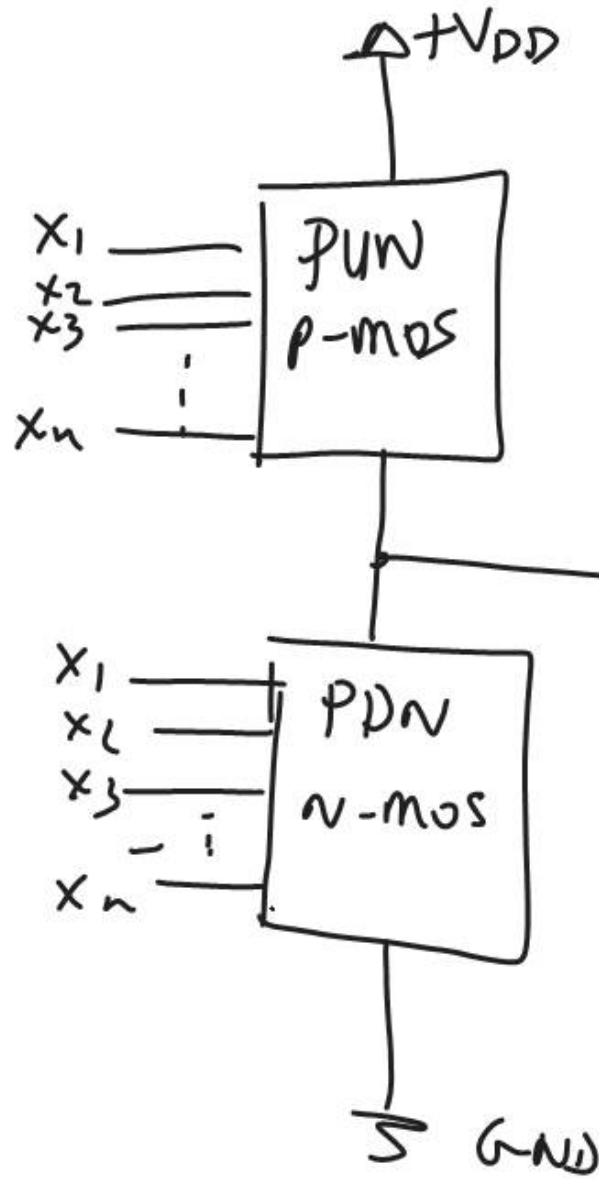




However, Nmos logic is not good regarding energy consumption, effectively utilizing the die area and technology etc ---

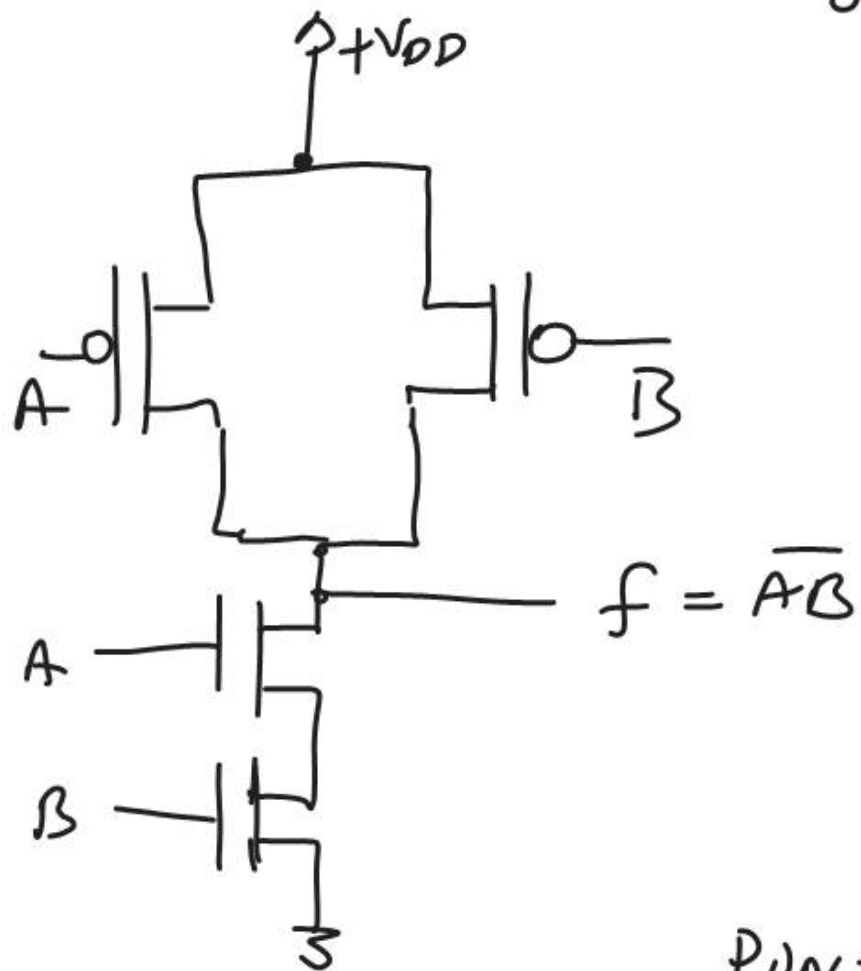
CMOS LOGIC GATE REALIZATIONS

PUN and PDN are DUAL



$$f(x_1, x_2, \dots, x_n) = \sum_{i=1}^n m_i(x_1, x_2, \dots, x_n)$$

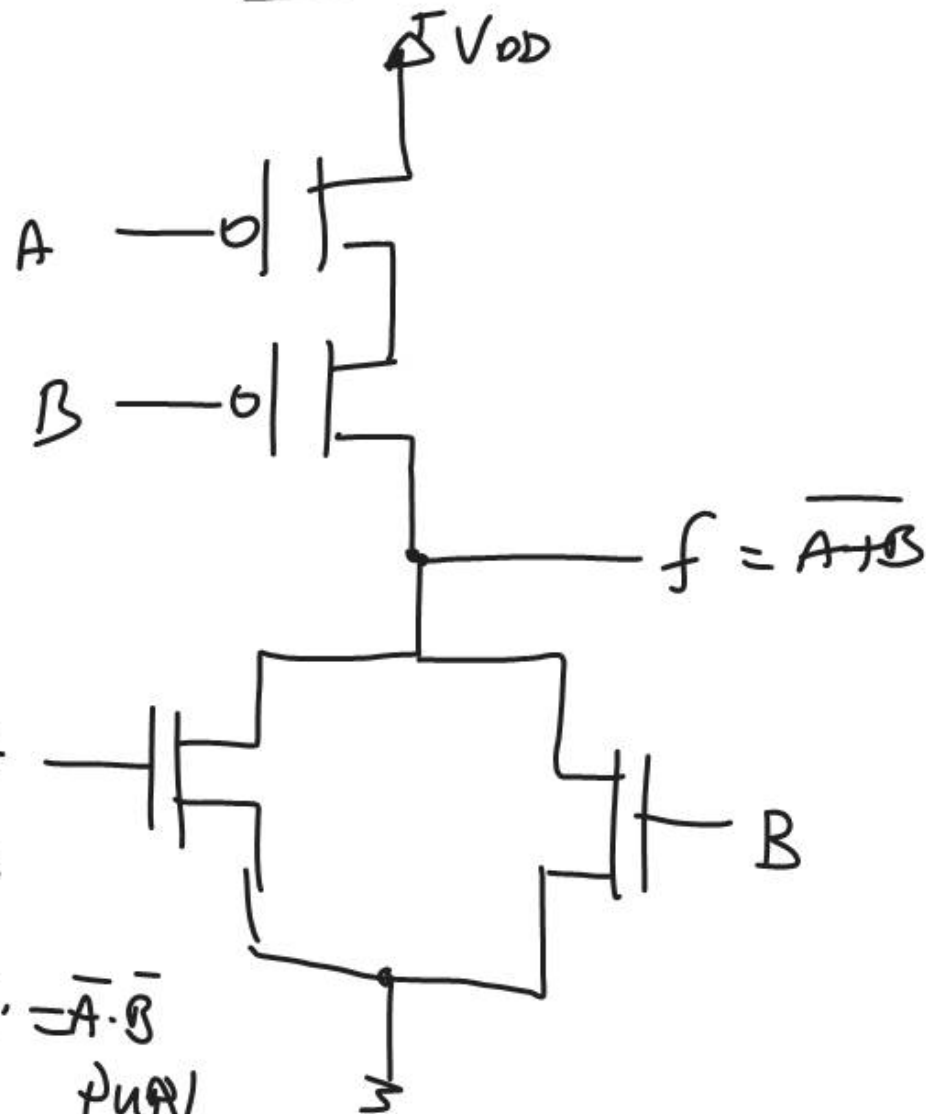
ex a CMOS NAND gate



$$\overline{AB} = \overline{A} + \overline{B}$$

$$\begin{aligned} P_{DN} &= AB \\ P_{UN} &= \overline{A} + \overline{B} \end{aligned} \quad \text{DUAL}$$

a NOR gate

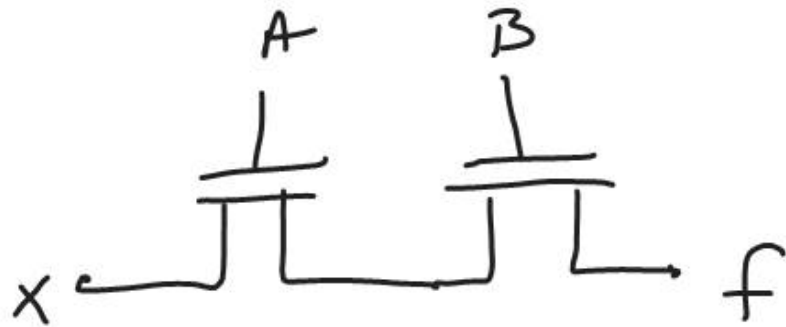


$$P_{DN} = A+B$$

$$\overline{P_{DN}} = \overline{A+B} = \overline{A} \cdot \overline{B}$$

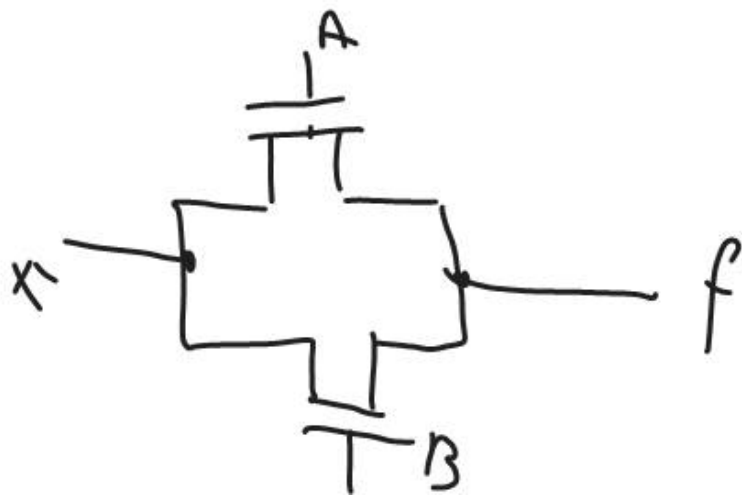
$$\begin{aligned} P_{UN} &= \overline{A} \cdot \overline{B} \\ \text{DUAL} \end{aligned}$$

NMOS TRANSISTORS in SERIES, PARALLEL CONNECTION



A	B	f
0	0	No change
0	1	" "
1	0	" "
1	1	x

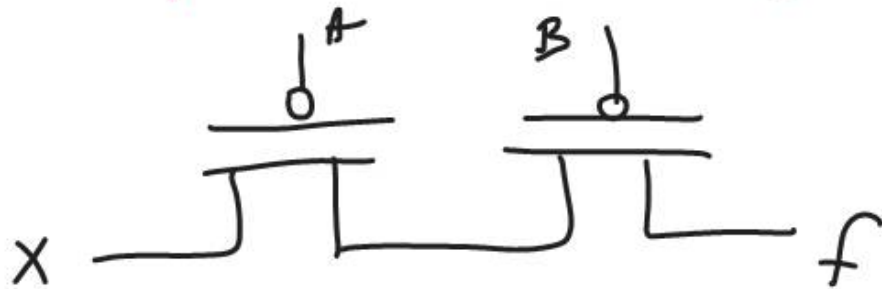
$$f = x \text{ if } A \cdot B = 1$$



A	B	f
0	0	No change
0	1	x
1	0	x
1	1	x

$$f = x \text{ if } A + B = 1$$

PMOS Transistors

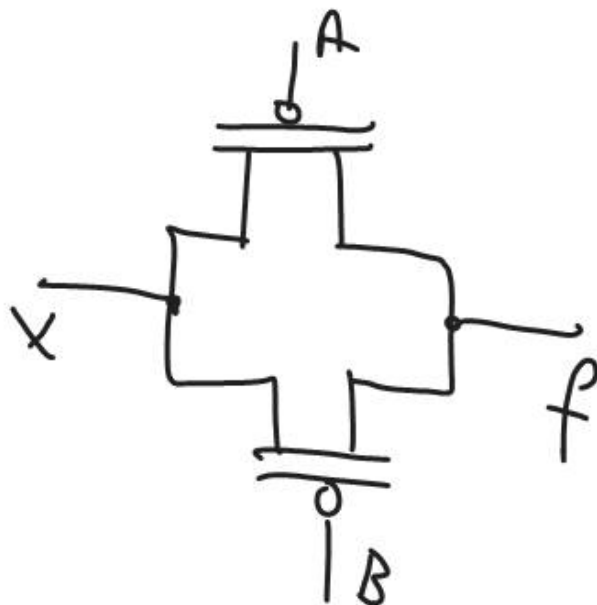


A	B	f
0	0	x
0	1	No change
1	0	,
1	1	,

$$f = x \quad \text{if}$$

$$\overline{A+B} = 1$$

$$\overline{A} \cdot \overline{B} = 1$$



A	B	f
0	0	x
0	1	x
1	0	x
1	1	No-change

$$f = x \quad \text{if} \quad \overline{A \cdot B} = 1$$

$$\overline{A} + \overline{B} = 1$$

QX

$$f = \overline{A \cdot (B + C) + D \cdot E}$$

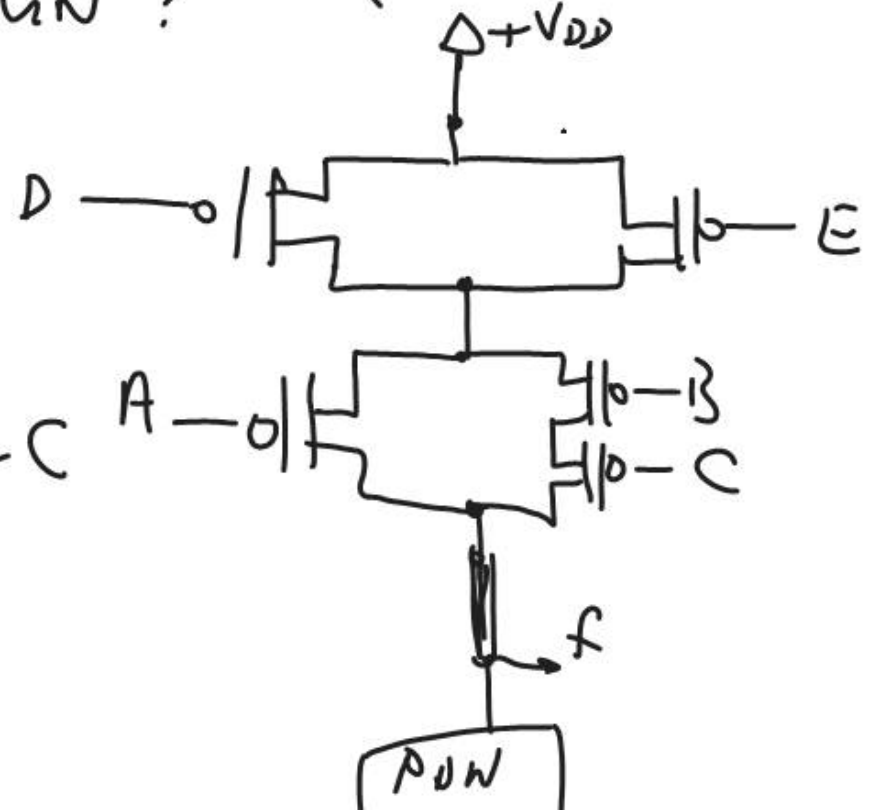
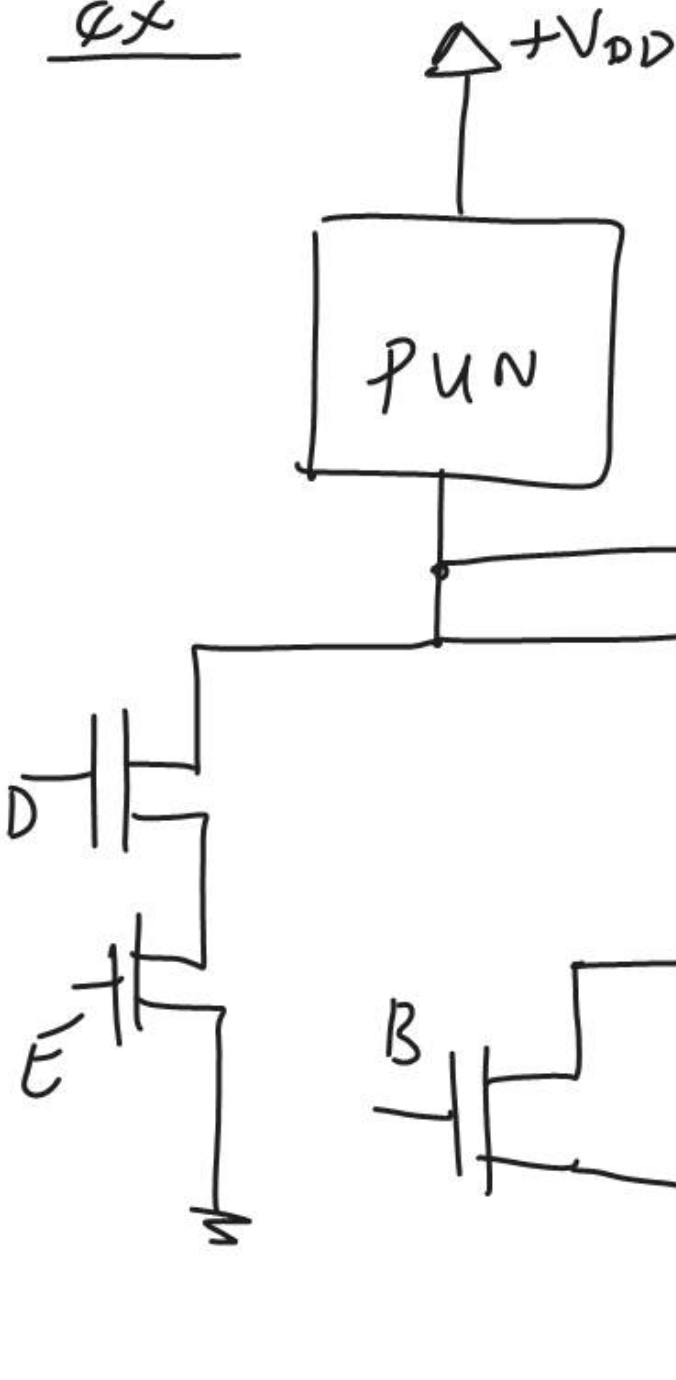
$$P_{UN} = \overline{A \cdot (B + C) \cdot (D \cdot E)}$$

$$= \overline{A} + \overline{(B + C)} \cdot (\overline{D} + \overline{E})$$

$$= (\overline{A} + \overline{B} \cdot \overline{C}) \cdot (\overline{D} + \overline{E})$$

a) $f = ?$

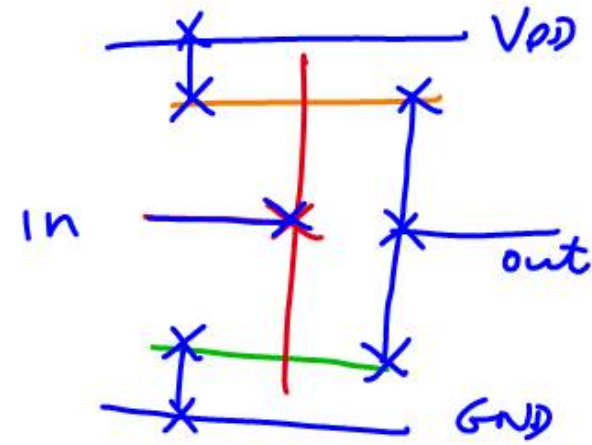
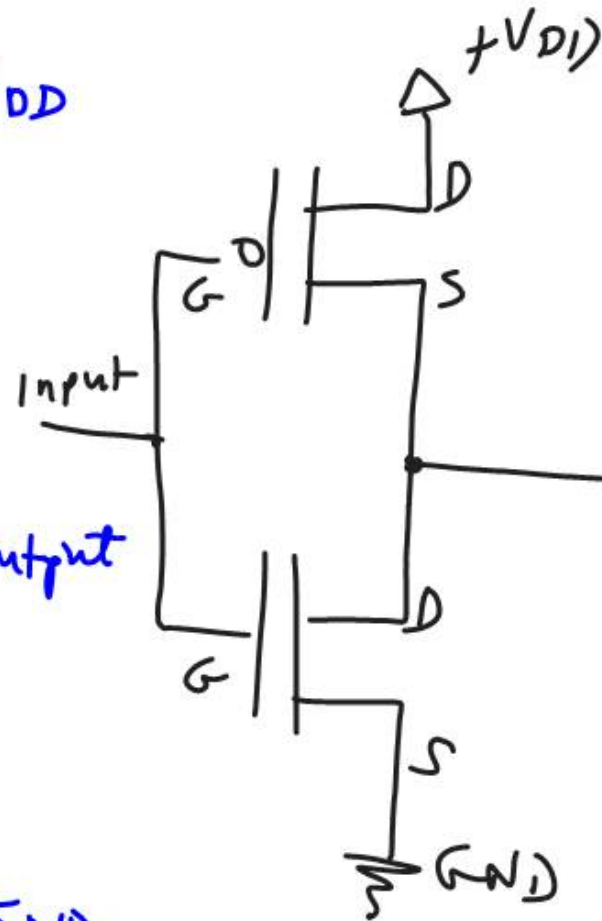
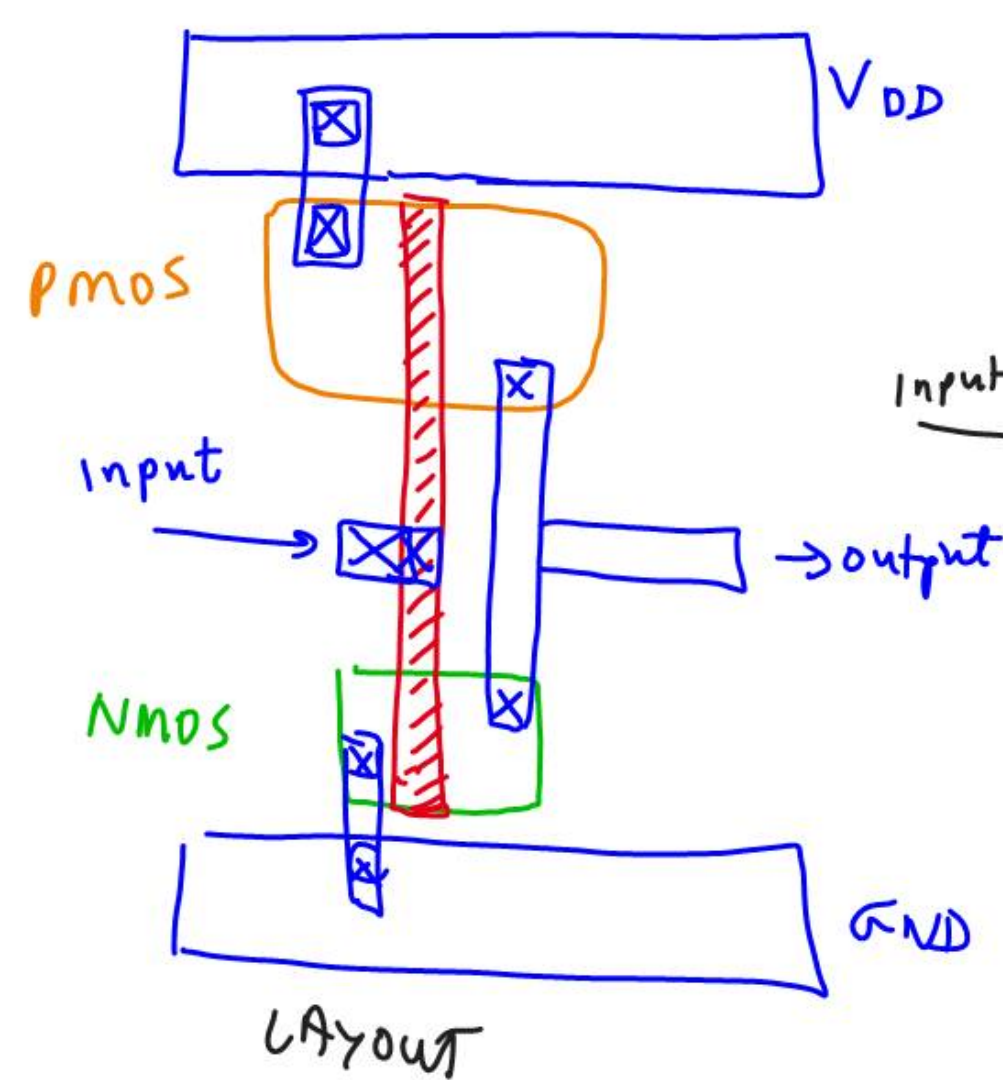
b) $P_{UN} ?$



STANDARD CELL LAYOUT METHODOLOGY

INVERTER

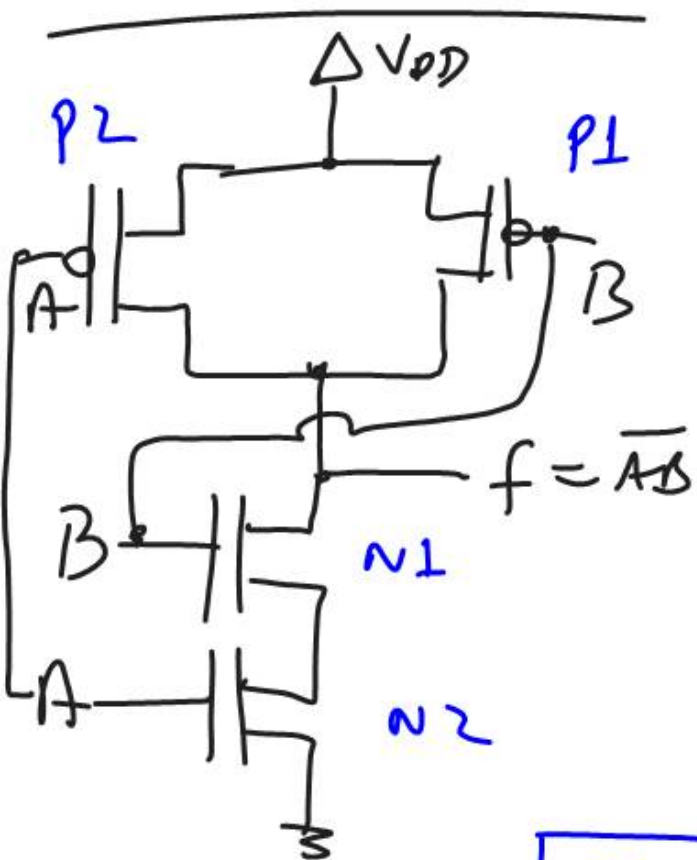
STICK DIAGRAM



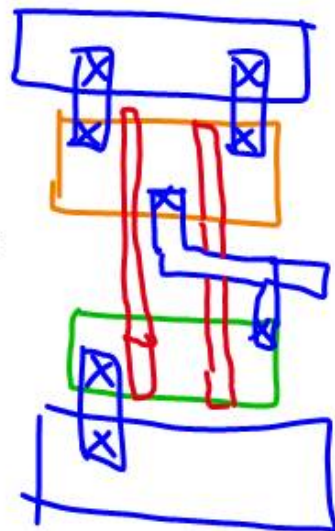
(CADERENCE)
Tool

(ICANT)

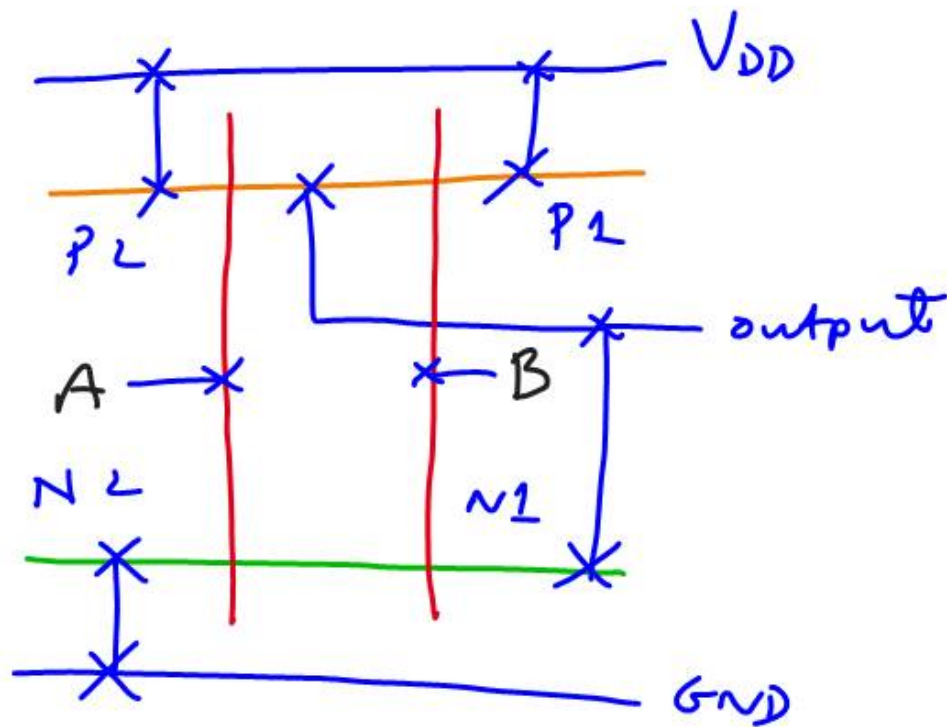
2 NAND



LAYOUT

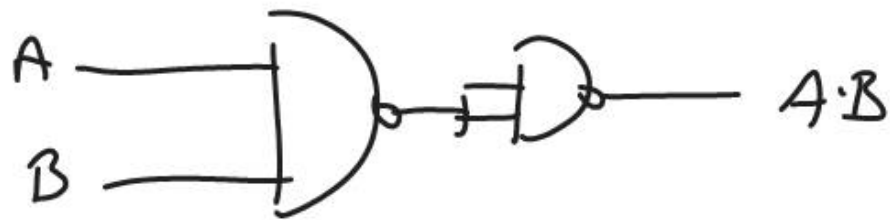


STICK DIAGRAM

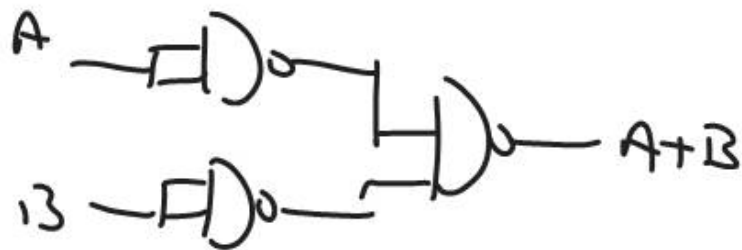


Since a logic function can be obtained by NAND gates only, we can create the logic functions by copy-pasting NAND layout and making the proper connections between them.

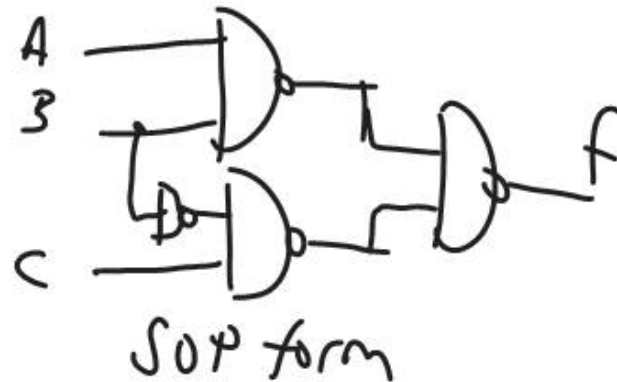
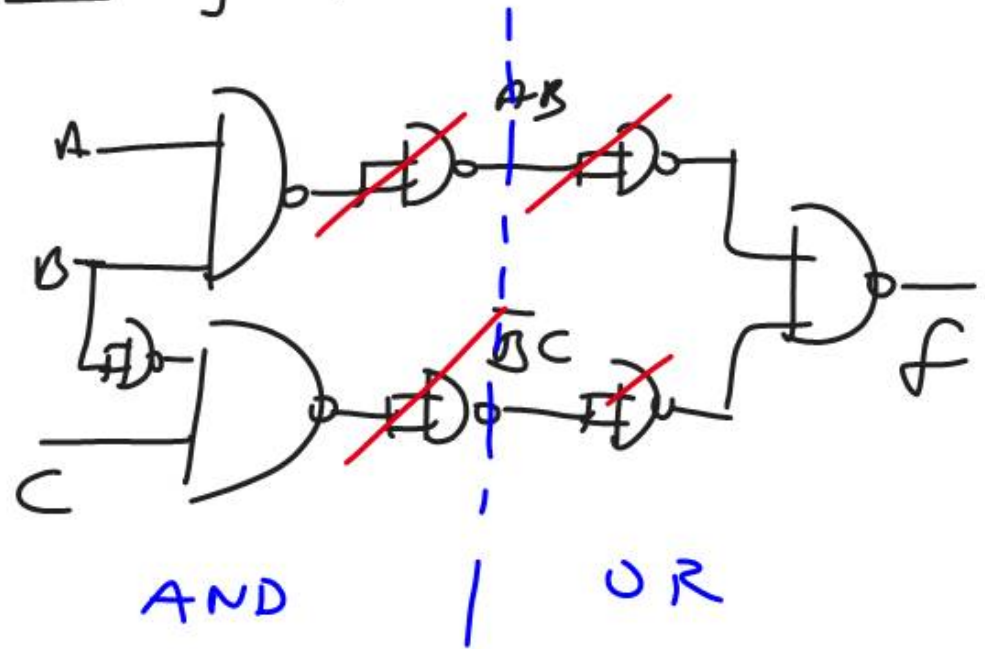
AND



OR



ex $f = AB + \bar{B}C$



HW #3

$$f = AB + BCD + \overline{A}CD$$

by using NOR gates only.

implement this function & draw the stick diagram
next week!